

Features

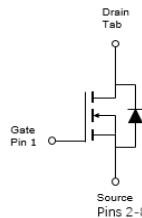
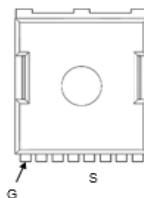
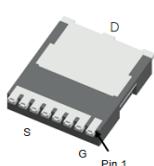
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{DS} Tested
- Halogen-free; RoHS-compliant

Product Summary

Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th)}_{Typ}$	2.9	V
$I_D(@V_{GS}=10V)$	454	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	0.82	$m\Omega$

Applications

- Load Switch
- PWM Application
- Power Management


PowerJE®10x12
Pin Assignment
Schematic Diagram
Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0801NTL-13	SH0801N	1	Tape&Reel	PowerJE®10x12	2000	10000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	454	A
		287	
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	2143	mJ
P_D	Power Dissipation	357	W
		143	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	34	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.1	2.9	3.8	V
$R_{\text{DS}(\text{ON})}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$	-	0.82	1.0	$\text{m}\Omega$
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	4.6	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $f = 1\text{MHz}$	-	14585	21878	pF
C_{oss}	Output Capacitance		-	5456	8185	pF
C_{rss}	Reverse Transfer Capacitance		-	130	261	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 40\text{V}$, $I_D = 20\text{A}$	-	222	-	nC
Q_{gs}	Gate Source Charge		-	69	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	49	-	nC
Switching Characteristics						
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{GS} = 10\text{V}$, $V_{DD} = 40\text{V}$ $I_D = 20\text{A}$, $R_{\text{GEN}} = 3\Omega$	-	37	-	ns
t_r	Turn-On Rise Time		-	70	-	ns
$t_{d(\text{off})}$	Turn-Off Delay Time		-	195	-	ns
t_f	Turn-Off Fall Time		-	102	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current	-	-	454	-	A
I_{SM}	Maximum Pulsed Body Diode Forward Current	-	-	1818	-	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 20\text{A}$	-		1.2	V
trr	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$, $\text{di}/\text{dt} = 100\text{A}/\text{us}$	65	131	196	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	367	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 40\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 37.8\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.

3. $R_{\theta\text{JA}}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.

4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

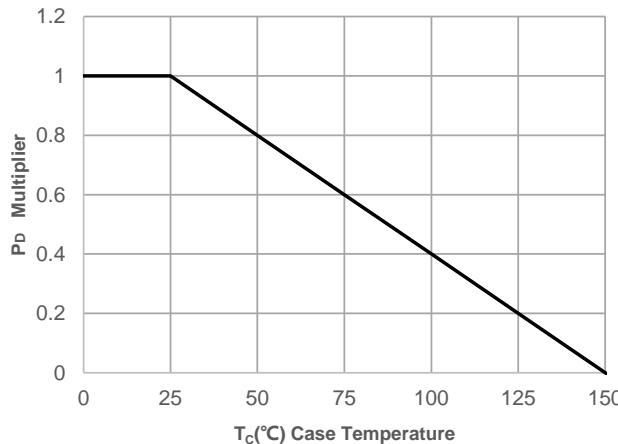


Figure 2: Current De-rating

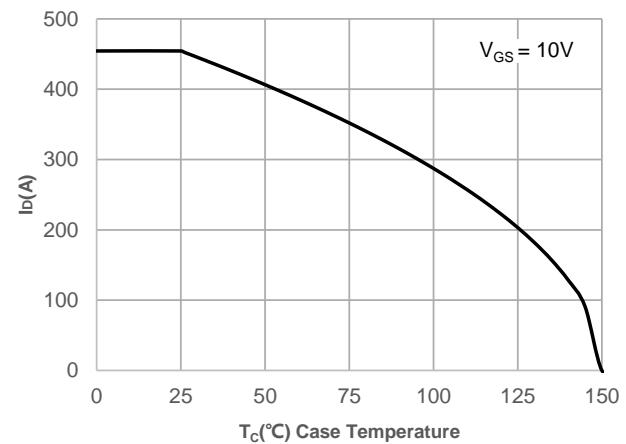


Figure 3: Normalized Maximum Transient Thermal Impedance

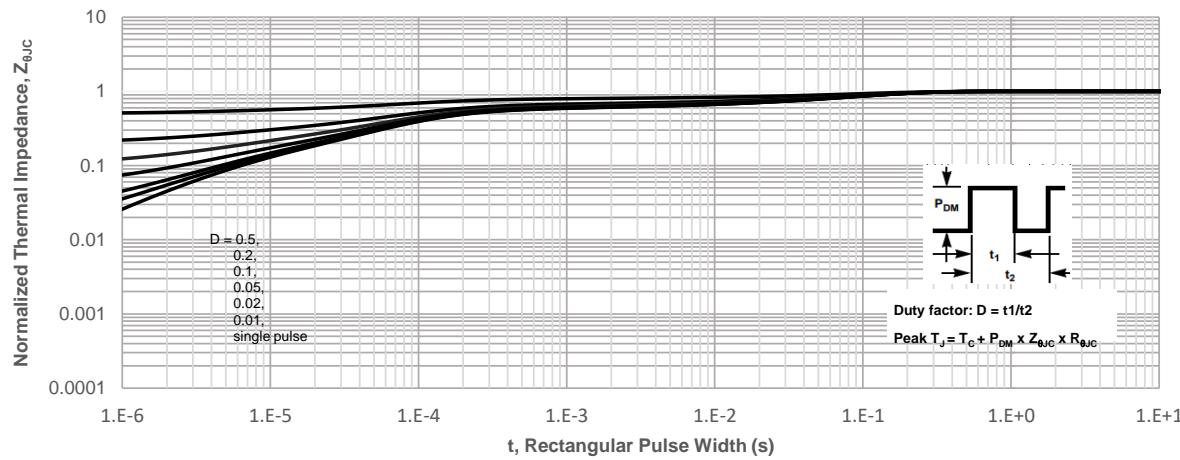
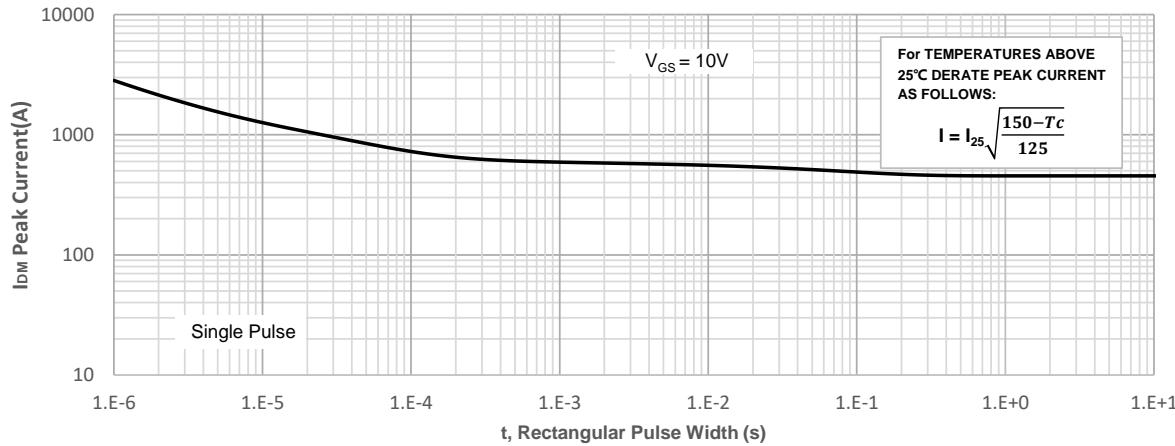


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

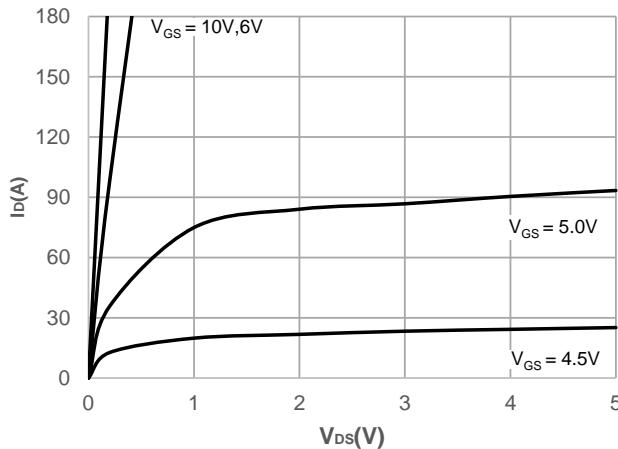


Figure 6: Typical Transfer Characteristics

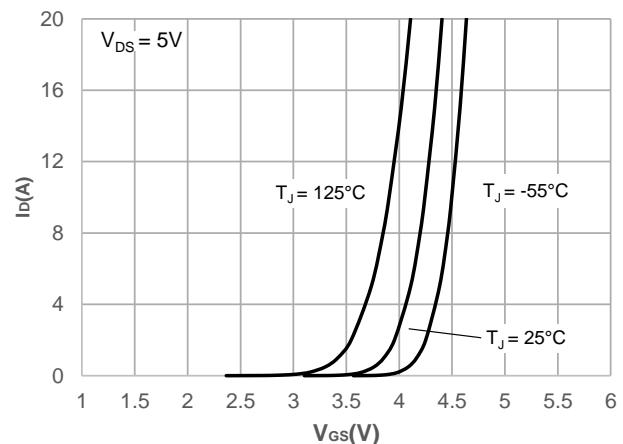


Figure 7: On-resistance vs. Drain Current

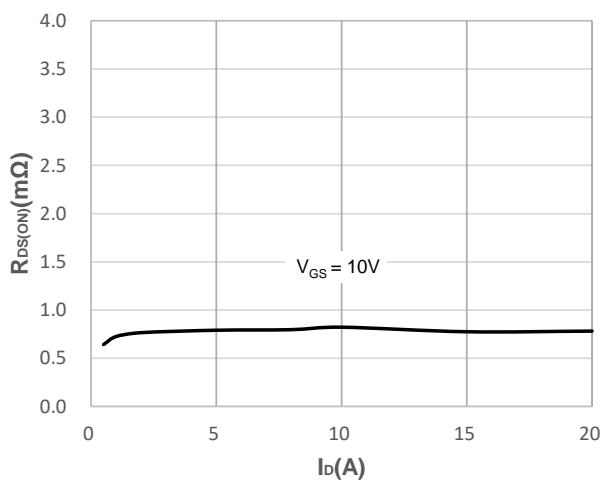


Figure 8: Body Diode Characteristics

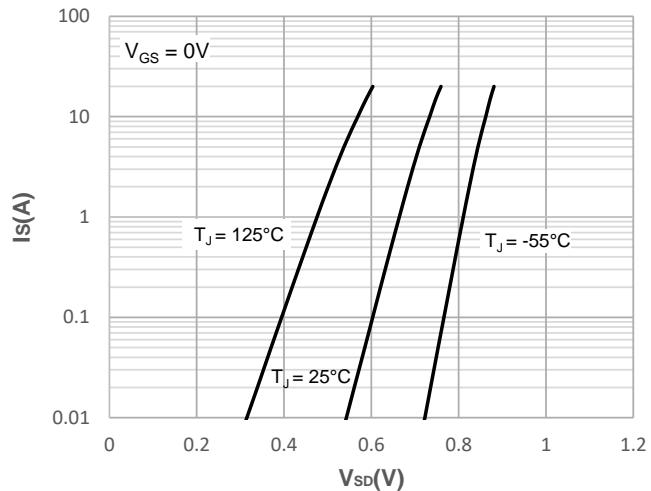


Figure 9: Gate Charge Characteristics

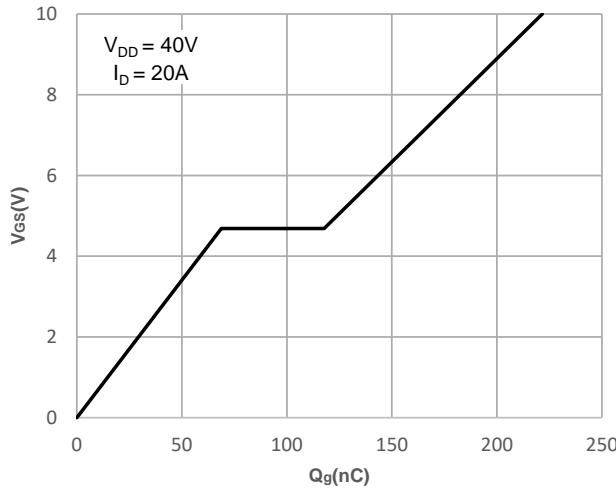
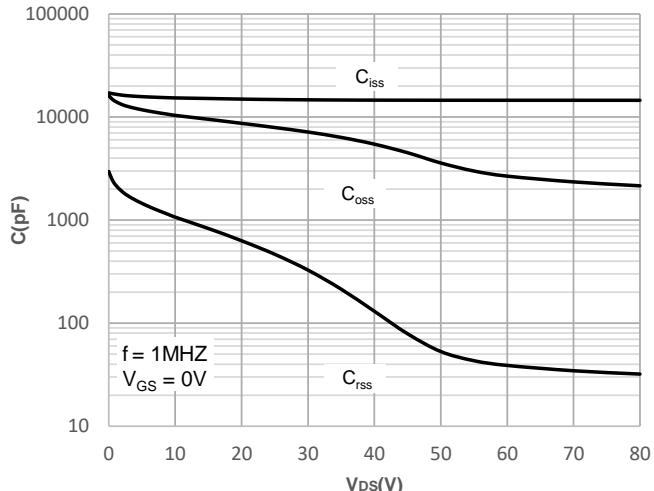


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

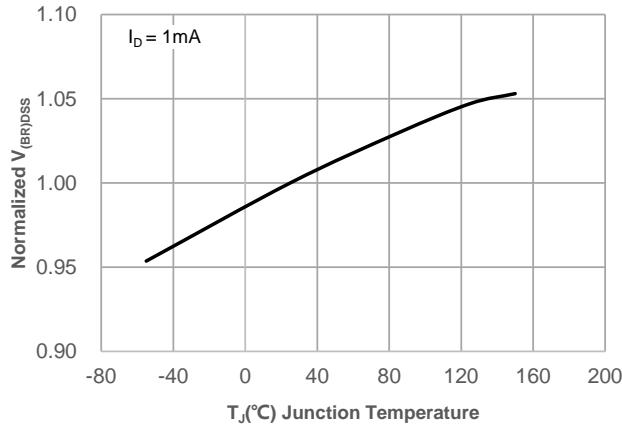


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

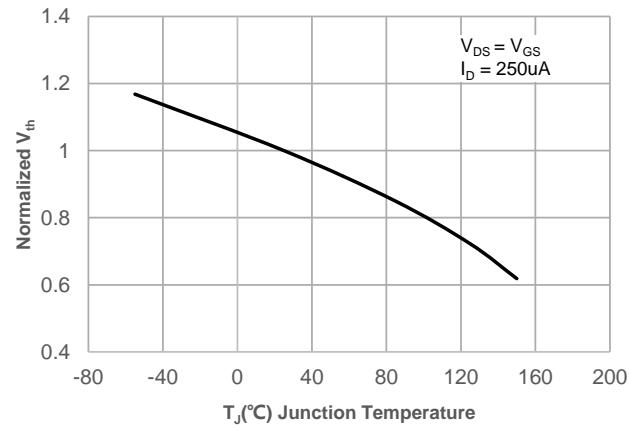


Figure 12: Normalized on Resistance vs. Junction Temperature

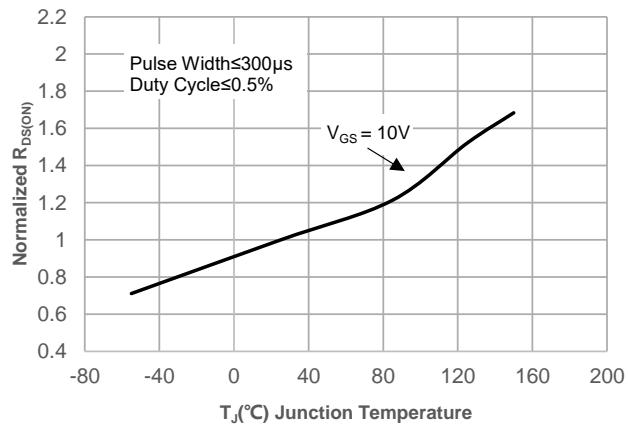


Figure 14: R_DS(ON) vs. V_GS

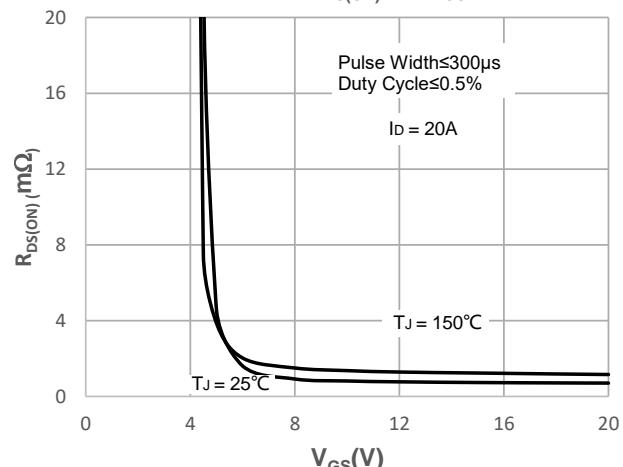
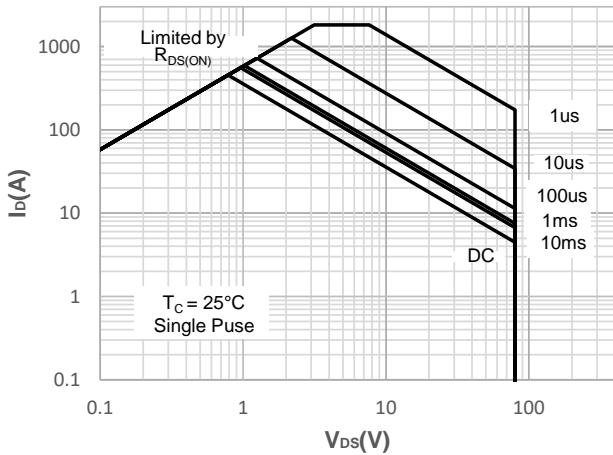


Figure 15: Maximum Safe Operating Area



Test Circuit

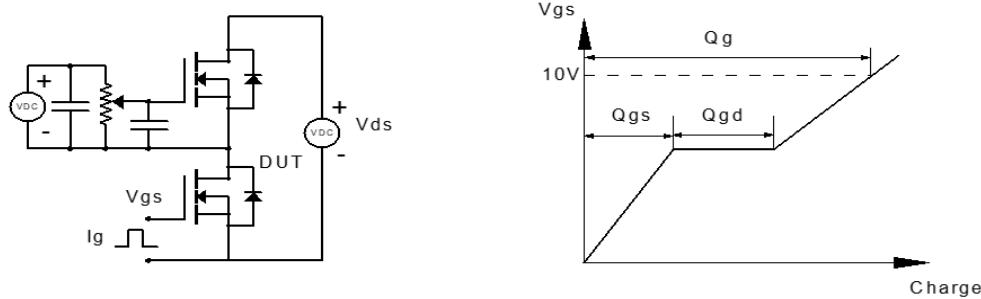


Figure 1: Gate Charge Test Circuit & Waveform

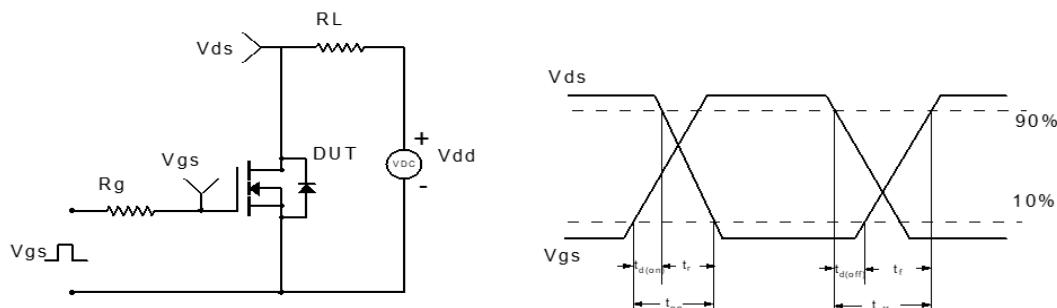


Figure 2: Resistive Switching Test Circuit & Waveform

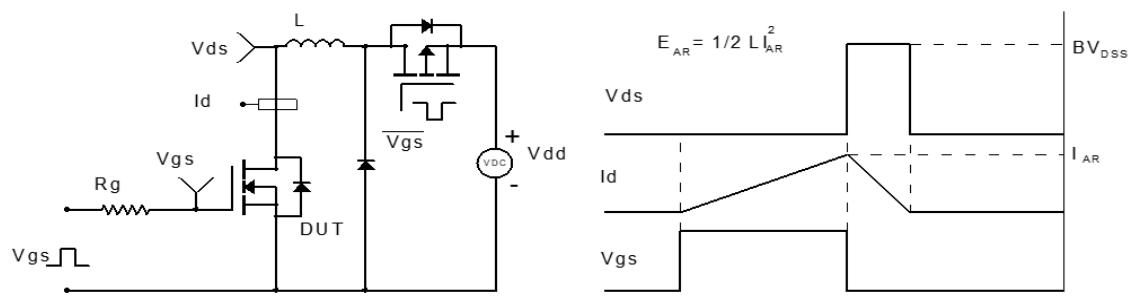


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

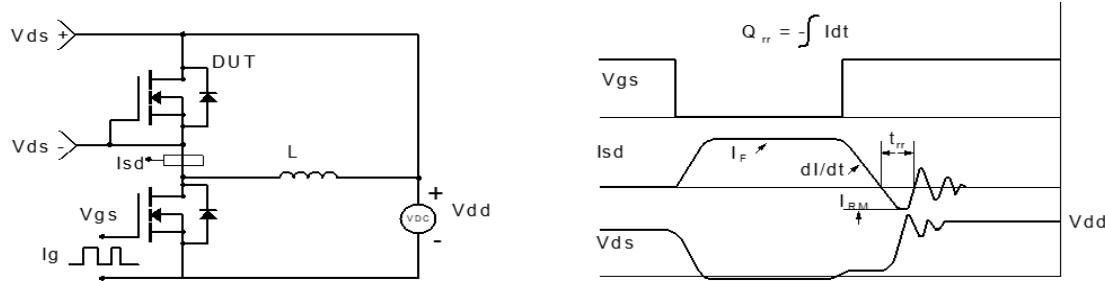
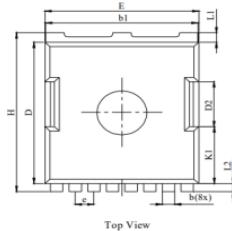


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PowerJE®10x12)

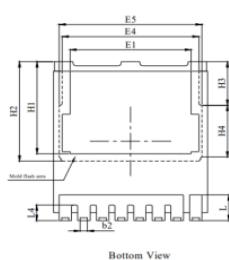
Package Outlines



Top View



Side View



Bottom View

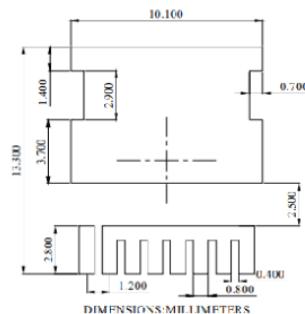
NOTES-

NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

DIM.	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.50
b	0.70	0.80	0.90
bl	9.70	9.80	9.90
b2	0.42	0.46	0.50
C	0.40	0.50	0.65
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e	1.20(BSC)		
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2		7.30	
H3		3.20	
H4		3.80	
K1		4.18	
L	1.70	1.90	2.10
L1		0.70	
L2		0.60	
L4	1.00	1.15	1.30

Recommended Soldering Footprint



DIMENSIONS: MILLIMETERS

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